

# SGM620A Low Power, Low Noise, Rail-to-Rail Output, Instrumentation Amplifier

#### GENERAL DESCRIPTION

The SGM620A is a high accuracy, high voltage instrumentation amplifier, which is designed to set any gain from 1 to 10000 with one external resistor. The device works well in battery-powered applications due to the low power consumption of 1.3mA typical quiescent current. The SGM620A provides SOIC-8 and TDFN-3×3-8L packages which are much smaller than discrete classical-three-OPAs circuits.

The SGM620A provides 120ppm (MAX) non-linearity and  $80\mu V$  (MAX) low input offset voltage. The device also features low noise, low bias current and low power. The combination of these characteristics makes it a good choice for applications requiring excellent DC performance.

The SGM620A offers  $6nV/\sqrt{Hz}$  low input voltage noise,  $300fA/\sqrt{Hz}$  input current noise at 1kHz, and  $0.4\mu V_{P-P}$  in the 0.1Hz to 10Hz band. It is suitable for pre-amplifier applications. The 10 $\mu$ s settling time to 0.01% makes SGM620A appropriate for multiplexed applications.

The SGM620A is available in Green SOIC-8 and TDFN-3×3-8L packages. It is specified over the extended -40°C to +125°C temperature range.

### **FEATURES**

- Single External Resistor Gain Set (Set Gain from 1 to 10000)
- Input Offset Voltage: 80µV (MAX)
- Input Bias Current: 15nA (TYP)
- Common Mode Rejection Ratio: 120dB (TYP) (G = 10)
- Input Voltage Noise: 6nV/√Hz at 1kHz
   0.1Hz to 10Hz Voltage Noise: 0.4uV<sub>P.P</sub>
- Bandwidth: 140kHz (G = 100)
- Settling Time to 0.01%: 10µs (G = 100)
- Rail-to-Rail Output
- Support Single or Dual Power Supplies:
   4.6V to 36V or ±2.3V to ±18V
- Low Power Supply Current: 1.3mA (TYP)
- -40°C to +125°C Operating Temperature Range
- Available in Green SOIC-8 and TDFN-3×3-8L Packages

#### **APPLICATIONS**

Precision Current Measurement
Pressure Measurement



### PACKAGE/ORDERING INFORMATION

MODEL	PACKAGE DESCRIPTION	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKING OPTION
SGM620A	SOIC-8	-40°C to +125°C	SGM620AXS8G/TR	SGM 620AXS8 XXXXX	Tape and Reel, 4000
3GIVIO2UA	TDFN-3×3-8L	-40°C to +125°C	SGM620AXTDB8G/TR	SGM 620ADB XXXXX	Tape and Reel, 4000

#### MARKING INFORMATION

NOTE: XXXXX = Date Code, Trace Code and Vendor Code.



Green (RoHS & HSF): SG Micro Corp defines "Green" to mean Pb-Free (RoHS compatible) and free of halogen substances. If you have additional comments or questions, please contact your SGMICRO representative directly.

#### **ABSOLUTE MAXIMUM RATINGS**

Supply Voltage, +V <sub>S</sub> to -V <sub>S</sub>	40V
Input Common Mode Voltage	±V <sub>S</sub>
Junction Temperature	+150°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (Soldering, 10s)	+260°C
ESD Susceptibility	
HBM	7000V
CDM	1000V

#### RECOMMENDED OPERATING CONDITIONS

Operating Temperature Range .....-40°C to +125°C

#### **OVERSTRESS CAUTION**

Stresses beyond those listed in Absolute Maximum Ratings may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect reliability. Functional operation of the device at any conditions beyond those indicated in the Recommended Operating Conditions section is not implied.

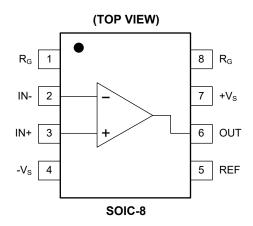
#### **ESD SENSITIVITY CAUTION**

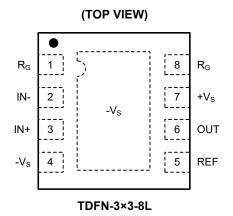
This integrated circuit can be damaged if ESD protections are not considered carefully. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because even small parametric changes could cause the device not to meet the published specifications.

#### **DISCLAIMER**

SG Micro Corp reserves the right to make any change in circuit design, or specifications without prior notice.

## **PIN CONFIGURATIONS**





## **PIN DESCRIPTION**

PIN	NAME	FUNCTION
1, 8	$R_G$	Gain Setting Pin. The gain can be set by placing the resistor across $R_G$ . $G = 1 + (49.4k\Omega/R_G)$ .
2	IN-	Inverting Input Pin.
3	IN+	Non-Inverting Input Pin.
4	-V <sub>S</sub>	Negative Power Supply Pin.
5	REF	Voltage Reference Pin. A voltage source with low impedance can be placed to supply this terminal in order to shift the output level.
6	OUT	Output Pin.
7	+V <sub>S</sub>	Positive Power Supply Pin.
Exposed Pad	-Vs	For TDFN-3×3-8L package, connect exposed pad to -V <sub>S</sub> .

## **ELECTRICAL CHARACTERISTICS**

 $(V_S = \pm 15V, R_L = 2k\Omega, Full = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ typical values are at } T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 

PARAMETER	SYMBOL	CONDITIONS		TEMP	MIN	TYP	MAX	UNITS
Gain (G = 1 + (49.4kΩ/R <sub>G</sub> ))								
Gain Range					1		10000	
			G = 1	+25°C		0.01	0.05	
			0 - 1	Full			0.1	
			G = 10	+25°C		0.1	0.2	
Gain Error (1)	GE	V <sub>OUT</sub> = -10V to +10V	0 - 10	Full			0.5	%
Call Life	OL.	V <sub>001</sub> = -10V to 110V	G = 100	+25°C		0.1	0.2	70
			G = 100	Full			0.5	
			G = 1000	+25°C		0.1	0.2	
			0 - 1000	Full			0.5	
Gain Temperature Coefficient			G = 1	Full		1		ppm/°C
Cam remperature Coemcient			G > 1	Full		20		ррпі/ С
			G = 1	+25°C		10	70	
			0 - 1	Full			100	
Non-Linearity			G = 10	+25°C		10	70	
		V <sub>OUT</sub> = -10V to +10V	G = 10	Full			100	nnm
				+25°C		10	70	ppm
			G = 100	Full			100	
			C = 1000	+25°C		20	120	
			G = 1000	Full			170	
Voltage Offset (Total RTI Error = \	V <sub>osi</sub> + V <sub>oso</sub> /(	G)						
Invest Officet Vallegge	W	\\ - \F\\\\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\		+25°C		30	80	μV
Input Offset Voltage	V <sub>osi</sub>	$V_S = \pm 5V$ to $\pm 15V$		Full			160	
Input Offset Voltage Drift	$\Delta V_{OSI}/\Delta T$			Full		0.2		μV/°C
Outrot Offert Vellere	.,	\\ .5\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		+25°C		200	700	
Output Offset Voltage	V <sub>oso</sub>	$V_S = \pm 5V$ to $\pm 15V$		Full			1200	μV
Output Offset Voltage Drift	$\Delta V_{OSO}/\Delta T$			Full		1.5		μV/°C
			G = 1	+25°C	110	120		dB
				Full	105			
				+25°C	125	130		
Offset Referred to the Input			G = 10	Full	122			
vs. Supply	PSRR	$V_S = \pm 2.3 V \text{ to } \pm 18 V$		+25°C	128	140		
			G = 100	Full	125			
				+25°C	128	140		
			G = 1000	Full	125			
Input Current		<u> </u>				1		
In and Direct Occurrent				+25°C		15	28	0
Input Bias Current	I <sub>B</sub>		Full			40	nA	
Average Temperature Coefficient of Input Bias Current	$\Delta I_B/\Delta T$			Full		0.15		nA/°C
Input Offset Current				+25°C		5	15	- A
•	los			Full			20	- nA
Average Temperature Coefficient of Input Offset Current	Δl <sub>os</sub> /ΔT			Full		0.05		nA/°C

NOTE: 1. Effects of external resistor  $R_{\text{\scriptsize G}}$  is not included.

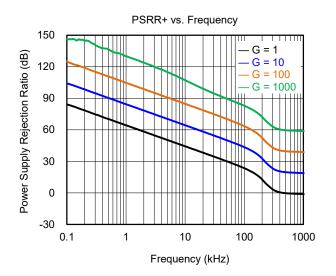
## **ELECTRICAL CHARACTERISTICS (continued)**

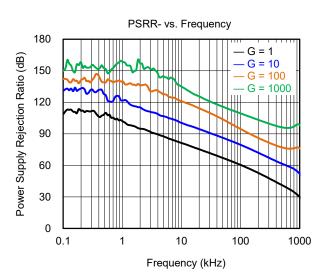
 $(V_S = \pm 15V, R_L = 2k\Omega, Full = -40^{\circ}C \text{ to } +125^{\circ}C, \text{ typical values are at } T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 

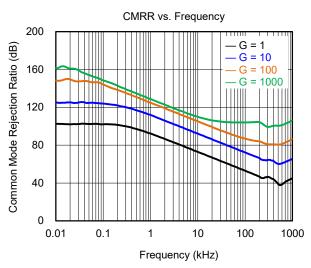
PAR	AMETER	SYMBOL	CONDITIO	NS	TEMP	MIN	TYP	MAX	UNITS
Input					•	·	r	,	1
Input	Differential	$Z_{DIFF}$			+25°C		10    4		GΩ    pl
Impedance	Common Mode	Z <sub>CM</sub>			+25°C		10    4		O12    pi
			V = 12.2V/4= 15V		+25°C	(-V <sub>S</sub> ) + 1.9		(+V <sub>S</sub> ) - 1.2	
Input Voltage Range			V <sub>S</sub> - 12.3V to 13V	$V_S = \pm 2.3 V$ to $\pm 5 V$		(-V <sub>S</sub> ) + 2.1		(+V <sub>S</sub> ) - 1.3	V
			$V_{\rm S} = \pm 5 \text{V to } \pm 18 \text{V}$		+25°C	(-V <sub>S</sub> ) + 1.9		(+V <sub>S</sub> ) - 1.4	v
			VS - 13V 10 110V		Full	(-V <sub>S</sub> ) + 2.1		(+V <sub>S</sub> ) - 1.4	
				G = 1	+25°C	80	100		
				<u> </u>	Full	77			
				G = 10	+25°C	100	120		
	e Rejection Ratio	CMRR	V <sub>CM</sub> = -10V to +10V		Full	92			dB
with 1kΩ Source	ce Imbalance	J	I Civi I Civi I Civi	G = 100	+25°C	105	130		
					Full	102			
				G = 1000	+25°C	105	130		
					Full	102			
Reference Inp		Ι _	Τ			1		1	<del></del>
Reference Inpu	ut Resistance	R <sub>REF</sub>			+25°C		18		kΩ
Reference Input Current		I <sub>REF</sub>	$V_{IN+} = V_{IN-} = 0V, V_{REF} = 0V$		+25°C Full		30	40	μA
			ALL THE STATE STATE					50	
Output Charae	cteristics	1			+25°C		0.40	100	<u> </u>
Output Voltage Swing		$V_{OH}$	$V_S = \pm 18V$ , $R_L = 2k\Omega$	$V_S = \pm 18V$ , $R_L = 2k\Omega$			310	400	
					Full		450	600	mV
		$V_{OL}$	$V_S = \pm 18V$ , $R_L = 2k\Omega$		+25°C		150	220	
					Full	40	0.4	300	<del>                                     </del>
Short-Circuit C	urrent	I <sub>SC</sub>	$I_{SC}$ $V_S = \pm 2.3 \text{V to } \pm 18 \text{V}, R_L = 50 \Omega \text{ to } V_S / 2$		+25°C	19	24		mA
Power Supply	•				Full	14			
rower Suppry	<u> </u>				+25°C		1.3	1.7	
Quiescent Curr	rent	IQ	$V_S = \pm 2.3V$ to $\pm 18V$ , $I_{OUT}$	2.3V to $\pm 18V$ , $I_{OUT} = 0A$			1.3	2.2	mA
Dynamic Resp	oonse	<u> </u>			Full			2.2	
				G = 1	+25°C		3900		
				G = 10	+25°C		1000		
Small-Signal -3	BdB Bandwidth	BW		G = 100	+25°C		140		kHz
				G = 1000					
01 D 1		0.0	V 4V 6		+25°C		17		
Slew Rate		SR	V <sub>OUT</sub> = 1V <sub>P-P</sub> Step	G = 1	+25°C		1.2		V/µs
Settling Time to	o 0.01%	ts	V <sub>OUT</sub> = 10V <sub>P-P</sub> Step	G = 1 to 100	+25°C		10		μs
Setting Time to 0.0 170				G = 1000	+25°C		51		μο
Noise		1	Т			T	1	1	ı
		e <sub>ni</sub>	f = 1kHz		+25°C		6		nV/√Hz
Output Voltage	Noise Density	e <sub>no</sub>	f = 1kHz		+25°C		80		nV/√Hz
				G = 1	+25°C		6		
0.411= += 4011=	Voltage Naine DT		f = 0.4117 to 4011-	G = 10	+25°C		1		,
U. IMZ 10 TUHZ	Voltage Noise, RTI		f = 0.1Hz to 10Hz	G = 100	+25°C		0.4		<u>μ</u> V <sub>P-P</sub>
				G = 1000	+25°C		0.4		
Input Current N	Noise Density, RTI	i <sub>n</sub>	f = 1kHz	1	+25°C		300		fA/√Hz
		*11	f = 0.1Hz to 10Hz		+25°C		15		pA <sub>P-P</sub>
.1Hz to 10Hz Current Noise, RTI f = 0.1Hz to 10Hz			+25 C		13		P\Ab⁻b		

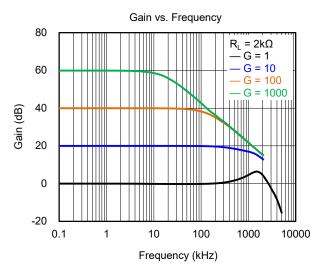
## TYPICAL PERFORMANCE CHARACTERISTICS

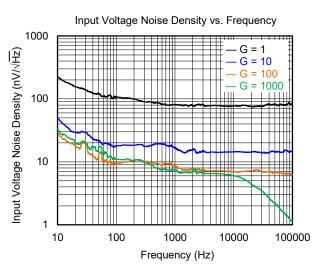
At  $T_A = +25$ °C,  $V_S = \pm 15$ V, unless otherwise noted.

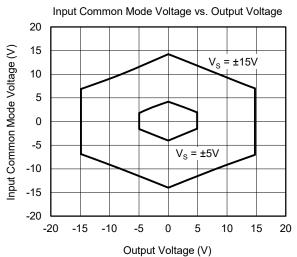






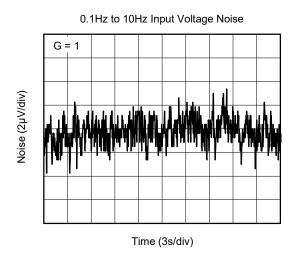


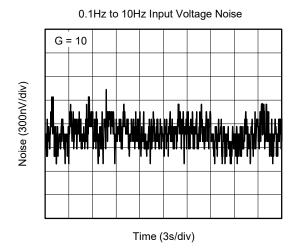


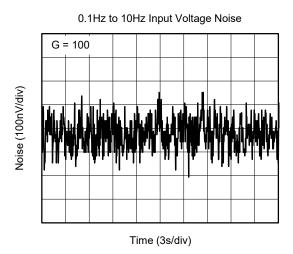


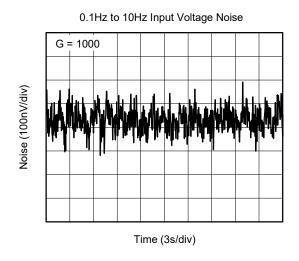
## **TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

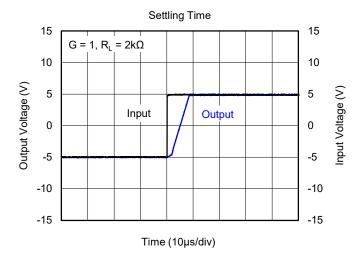
At  $T_A$  = +25°C,  $V_S$  = ±15V, unless otherwise noted.

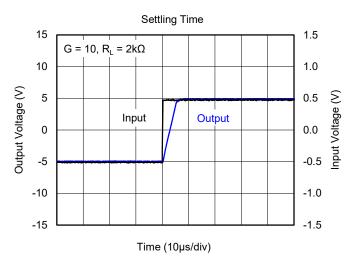






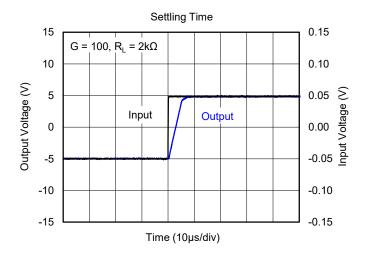


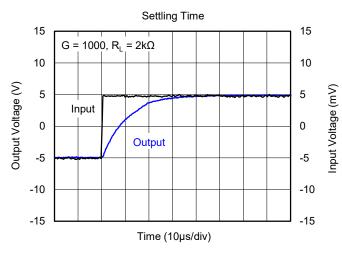




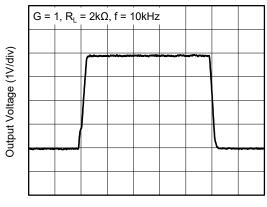
## **TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

At  $T_A = +25$ °C,  $V_S = \pm 15$ V, unless otherwise noted.



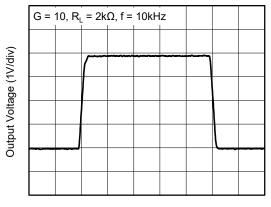


Large-Signal Step Response



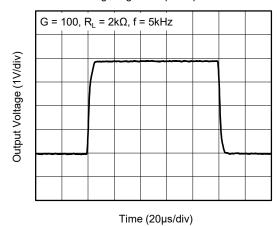
Time (10µs/div)

Large-Signal Step Response

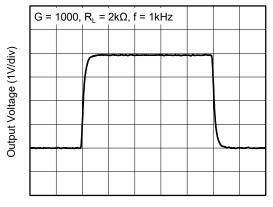


Time (10µs/div)

Large-Signal Step Response



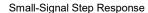
Large-Signal Step Response

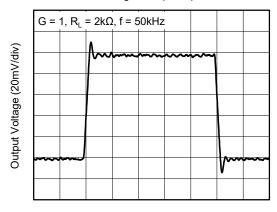


Time (100µs/div)

## **TYPICAL PERFORMANCE CHARACTERISTICS (continued)**

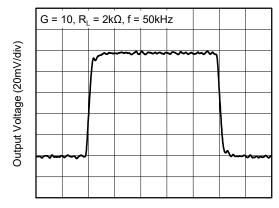
At  $T_A = +25$ °C,  $V_S = \pm 15$ V, unless otherwise noted.





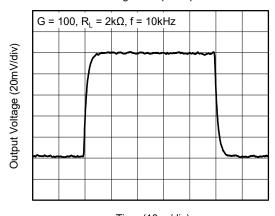
Time (2µs/div)

#### Small-Signal Step Response



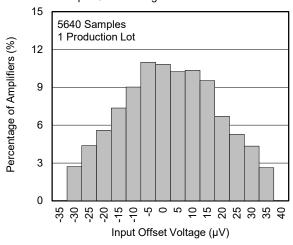
Time (2µs/div)

#### Small-Signal Step Response

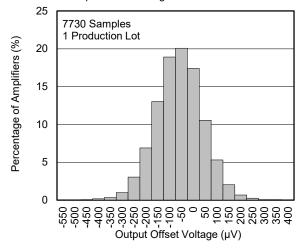


Time (10µs/div)

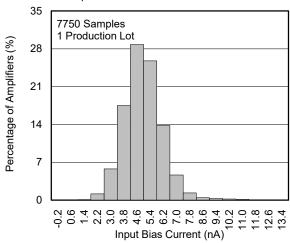
#### Input Offset Voltage Production Distribution



Output Offset Voltage Production Distribution



Input Bias Current Production Distribution



## **OPERATION THEORY**

The SGM620A is modified with the classic three-op-amp and it is a holistic instrumentation amplifier.

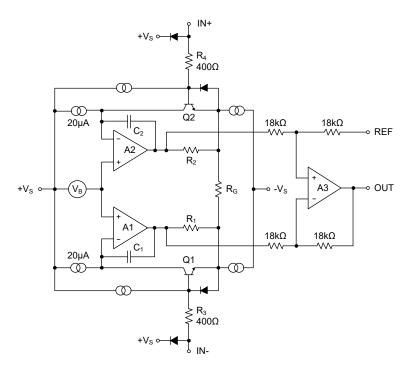


Figure 1. Simplified Schematic

The high precision input is provided by the two input transistor Q1 and Q2 (Figure 1) and this results in 10 × lower bias current of the input pins. The constant collector current of Q1 and Q2 is maintained by the two loops Q1-A1-R1 and Q2-A2-R2, so the input voltage is impressed across the gain setting resistor  $R_{\rm G}$  of the amplifier. The differential gain from A1/A2 outputs can be expressed by G = 1+  $(R_1+R_2)/R_{\rm G}$ . The unity-gain subtractor (A3) can reject the common mode signal so that SGM620A produces a single-ended output with REF pin biased.

The transconductance of the pre-amplifier is determined by the resistance of  $R_{\text{G}}$ . The transconductance will increase gradually to that of the input transistors if the resistance of  $R_{\text{G}}$  is reduced for larger gains. The important benefits are shown below:

• Boosting the open-loop gain can also increase the programmed gain, so that the related error of gain is reduced.

- The gain-bandwidth product which is determined by the two capacitors C<sub>1</sub>, C<sub>2</sub> and the transconductance of the pre-amplifier can increase with programmed gain, so that the frequency response is enhanced.
- Reducing the input voltage noise to  $6nV/\sqrt{Hz}$ , and it is determined by the base resistance and the collector current of the input.

The integrated resistors ( $R_1$  and  $R_2$ ) inside the SGM620A are set to 24.7k $\Omega$ , so that the gain can be programmed with the external resistor  $R_G$ .

The equation of gain is shown as below:

$$G = \frac{49.4k\Omega}{R_G} + 1$$

$$R_G = \frac{49.4k\Omega}{G - 1}$$

## **APPLICATION INFORMATION**

#### **Pressure Measurement**

SGM620A is widely used in the application of bridge, such as measuring the pressure in weigh scales. It is also suitable for detecting the pressure sensor with higher resistance due to high input impedance.

Figure 2 shows the pressure transducer bridge of  $5k\Omega$  which is powered by a 5V single supply. In such a circuit, the bridge consumes only 1mA. The buffered voltage divider and SGM620A can condition the output signal with typical 3.3mA supply current.

The advantage of small size for SGM620A is attractive for the transducers of pressure. Because of the low noise and drift, it can also be used in the application of diagnostic non-invasive blood pressure measurement.

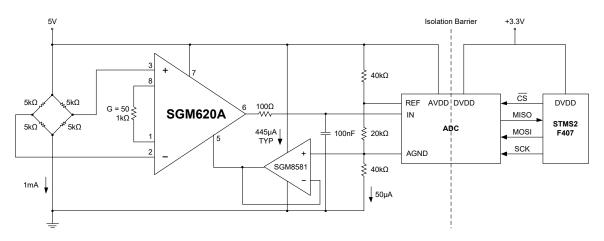


Figure 2. The Operation of the Pressure Monitor Circuit with 5V Single Supply

#### **Medical ECG Amplifier**

Because of the advantage of low current noise, SGM620A can be used in ECG monitors (Figure 3) where the source resistances can reach  $1M\Omega$  or higher. It is the best choice to use SGM620A in the battery-powered data recorders as it can operate on the condition of low supply voltage, low power and space-saving packages.

Moreover, for better performance, combining with the advantages of low voltage noise, low current and low bias currents can enhance the dynamic range of SGM620A.

The stability of the right leg drive loop can be maintained by the capacitor  $C_1$ . Moreover, for protecting the patient from the possible harm, the isolation safeguards should be added between the patient and the circuit part.

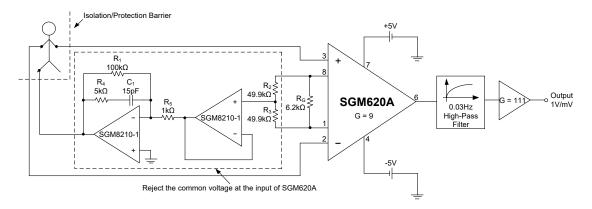


Figure 3. The Circuit of Medical ECG Monitor

## **APPLICATION INFORMATION (continued)**

#### **Precision V-I Converter**

It's easy to realize a precision current source (Figure 4) utilizing one SGM620A, another operational amplifier and two resistors. To obtain a better CMRR of SGM620A, a buffer should be placed between the REF pin and the OUT pin of the amplifier. The equation which is shown in Figure 4 illustrates the output current of the circuit.

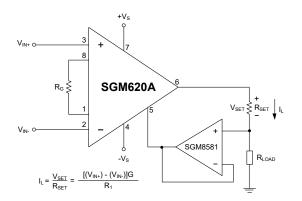


Figure 4. Precision Voltage-to-Current Converter

## **Input and Output Offset Voltage**

Two main sources which are error of input and output result in the low errors of SGM620A. When referred to the input, the output error should be divided by the gain of the instrumentation amplifier. From the equations which are shown as below, the input error takes a leading position at large gains while the output error takes a leading position at small gains.

Total Error Referred to Input (RTI) = Input Error + (Output Error/G)

Total Error Referred to Output (RTO) = (Input Error × G) + Output Error

#### **Terminal of Reference**

Potential of the reference terminal defines the zero output voltage. It becomes extremely useful while the load is not tied to the precise ground of the rest of the system. The reference terminal provides one way to bias a precise voltage to the output, and the reference voltage should be in the range of 2V within the supply voltages. On top of these, to keep better CMRR, the parasitic resistor at this pin should be low.

#### Selection of Gain

The gain of the instrumentation amplifier is determined by the external resistor  $R_{\rm G}.$  The accuracy of the external resistor  $R_{\rm G}$  is important as it may influence the error of gain. It is recommended that selecting the resistor with 0.1% or 1% precision is a good choice. The following table shows the gain effect with the selection of 1% or 0.1% precision resistor. Also, leaving the pin 1 and pin 8 (the place of  $R_{\rm G}$ ) open can make the gain of SGM620A equals to 1.

$$R_{G} = \frac{49.4k\Omega}{G - 1}$$

As mentioned before, the gain error can be minimized by equivalent parasitic resistor in series with  $R_{\rm G}$ . Moreover, low TC of 1ppm/°C is required for the selection of  $R_{\rm G}$  to avoid the gain drift of SGM620A.

Table 1. Different Values for Gain Resistor

1% STD Table Value of $R_G(\Omega)$	Calculated Gain	0.1% STD Table Value of $R_G(\Omega)$	Calculated Gain
49.9k	1.990	49.3k	2.002
12.4k	4.984	12.4k	4.984
5.49k	9.998	5.49k	9.998
2.61k	19.93	2.61k	19.93
1.00k	50.40	1.01k	49.91
499	100.0	499	100.0
249	199.4	249	199.4
100	495.0	98.8	501.0
49.9	991.0	49.3	1003.0

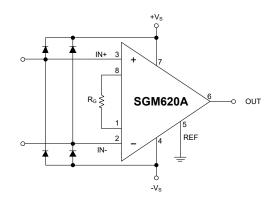


Figure 5. Diode for Protecting  $V_{\text{IN}}$  from Larger than  $V_{\text{S}}$ 

## **APPLICATION INFORMATION (continued)**

#### **RF** Interference

One of the characteristics of instrumentation amplifier is rectifying the small signal which is out of the band. This kind of disturbance can be described as the small biased voltage. All of the high frequency components can be filtered by the R-C network which is placed in the input position of the instrumentation amplifier, as shown in Figure 6. The following equation shows the equation of filtering frequency for the differential and common mode part of the input signal.

$$\begin{aligned} \text{FilterFreq}_{\text{DIFF}} &= \frac{1}{2\pi R \left(2C_{\text{D}} + C_{\text{C}}\right)} \\ &\text{FilterFreq}_{\text{CM}} &= \frac{1}{2\pi R C_{\text{C}}} \end{aligned}$$

 $C_D \ge 10C_C$  is required in the above equation.

The capacitor  $C_D$  influences the quality of the differential signal, while  $C_C$  influences the quality of the common mode signal. The common mode rejection ratio would be reduced if the  $R \times C_C$  is mismatched. To reduce this negative influence and obtain a good CMRR, it is recommended that the capacitance of  $C_D$  should be 10 times larger than  $C_C$ . To conclude, the larger the ratio of  $C_D$ : $C_C$  is, the less negative influence to the circuit.

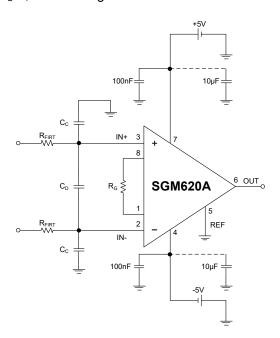


Figure 6. One Method to Reduce the Interference of RF

#### **Common Mode Rejection**

The common mode rejection ratio of the instrumentation amplifier is high as it can measure the differential signal between the two inputs when both IN+ and IN- increase or decrease equally. Also, this specification can be defined in the whole range of input voltage.

To obtain a best CMRR, it is recommended that the REF pin should be connected to a low impedance input and the difference of impedance between two inputs should be as small as possible. Also, using shielded cable can effectively reduce the noise of the circuit, and it should be driven properly for better value of CMRR. The following two figures (Figure 7 and Figure 8) illustrate the method to increase the CMRR for alternating circuit by bootstrapping the capacitance of the shielded cable, and this kind of method can also reduce the mismatching of capacitance at the inputs.

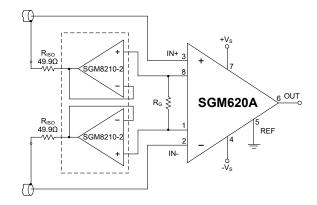


Figure 7. Differential Input Shield Driving

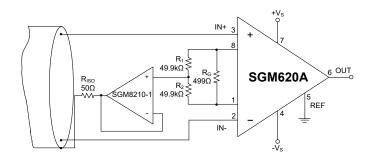


Figure 8. Common Mode Input Shield Driving

## **APPLICATION INFORMATION (continued)**

### **Isolation of Grounding**

For solving the problems of grounding, REF pin should be connected to the "local ground" as the output of the instrumentation amplifier is biased with  $V_{\text{REF}}$ .

Because of the noisy environment of the digital circuit, the component of data-acquisition such as Analog Digital Converter (ADC) has two pins which are AGND and DGND. Also, the isolation can be made by using a single line or  $0\Omega$  resistor. However, each returns of ground should be separated so that the current flow from the sensitive point could be minimized. Also, the ground returns between analog and digital should be tied together with one point, which is shown in ADC part of Figure 9.

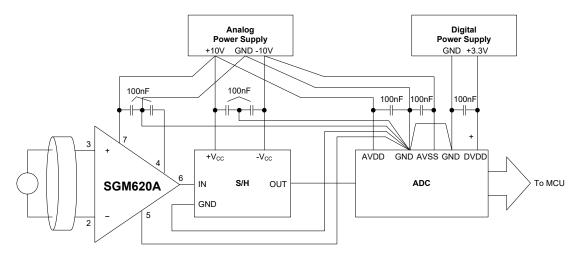


Figure 9. Isolation of Grounding

## Return of Grounding for IB

The bias current ( $I_B$ ) at the inputs is needed for operating and biasing the transistor at the input stage of the instrumentation amplifier, so it is also necessary to design a ground return path for the bias current. For example, for operating the floating inputs of the amplifier (see Figure 10  $\sim$  12), such as AC-coupled transformer, there should be an electrical line between the input and the ground for ground return of bias current.

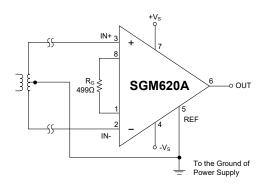


Figure 10. Return of Grounding for  $I_{\mbox{\scriptsize B}}$  with Transformer-Coupled Inputs

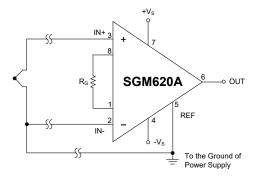


Figure 11. Return of Grounding for I<sub>B</sub> with Thermocouple Inputs

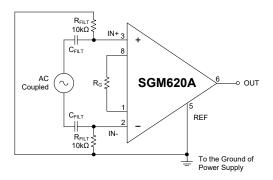


Figure 12. Return of Grounding for I<sub>B</sub> with AC-Coupled Input



# Low Power, Low Noise, Rail-to-Rail Output, Instrumentation Amplifier

Page

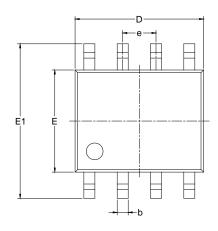
## SGM620A

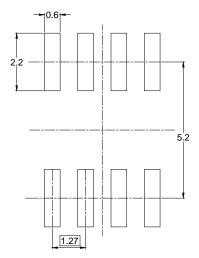
## **REVISION HISTORY**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

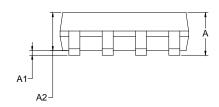
Changes from Original (MARCH 2024) to REV.A

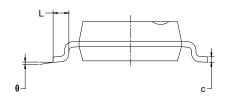
# **PACKAGE OUTLINE DIMENSIONS SOIC-8**





RECOMMENDED LAND PATTERN (Unit: mm)

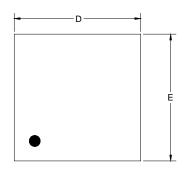


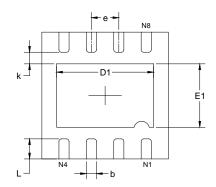


Symbol		nsions meters	Dimensions In Inches		
	MIN MAX		MIN	MAX	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
Е	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.27	27 BSC 0.0		50 BSC	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

- Body dimensions do not include mode flash or protrusion.
   This drawing is subject to change without notice.

# **PACKAGE OUTLINE DIMENSIONS TDFN-3×3-8L**

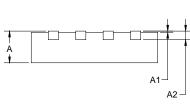




**TOP VIEW** 

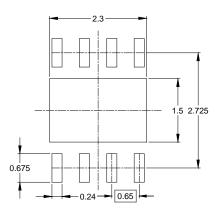


**BOTTOM VIEW** 





**SIDE VIEW** 



RECOMMENDED LAND PATTERN (Unit: mm)

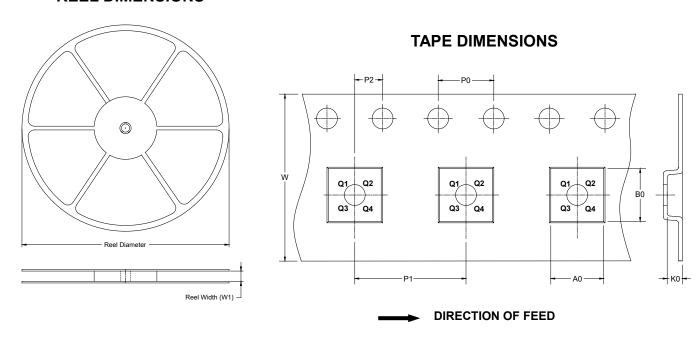
Symbol		nsions meters	Dimensions In Inches		
	MIN	MIN MAX		MAX	
Α	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A2	0.203	REF	REF 0.008 REF		
D	2.900	3.100	0.114	0.122	
D1	2.200	2.400	0.087	0.094	
E	2.900	3.100	0.114	0.122	
E1	1.400	1.600	0.055	0.063	
k	0.200	MIN	0.008	3 MIN	
b	0.180	0.300	0.007	0.012	
е	0.650	) TYP	0.026	TYP	
L	0.375	0.575	0.015	0.023	

NOTE: This drawing is subject to change without notice.



## TAPE AND REEL INFORMATION

#### **REEL DIMENSIONS**

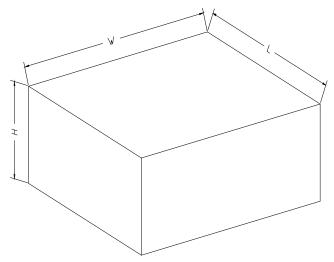


NOTE: The picture is only for reference. Please make the object as the standard.

#### **KEY PARAMETER LIST OF TAPE AND REEL**

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
SOIC-8	13"	12.4	6.40	5.40	2.10	4.0	8.0	2.0	12.0	Q1
TDFN-3×3-8L	13"	12.4	3.35	3.35	1.13	4.0	8.0	2.0	12.0	Q1

## **CARTON BOX DIMENSIONS**



NOTE: The picture is only for reference. Please make the object as the standard.

## **KEY PARAMETER LIST OF CARTON BOX**

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
13"	386	280	370	5